

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

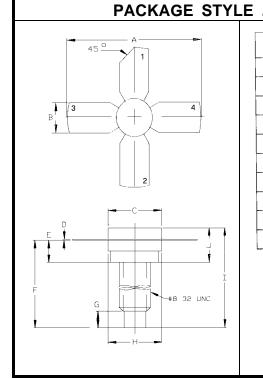
The **ASI PT9701B** is a Common Emitter Device Designed for Class A , AB and C Amplifier Applications in the 225 - 400 MHz Military Communications Band.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- High Gain

MAXIMUM RATINGS

Ic	1.25 A
V _{CES}	45 V
P _{DISS}	14 W @ $T_C = 25$ $^{\circ}C$
TJ	-55 °C to +200 °C
T _{STG}	-55 °C to +200 °C
¶ JC	12 ^O C/W



B .220/5,59 .2	55/26.80 				
	230/5,84				
	.230/5,84				
.270/6.86	.285/7,24				
D .003/0,08 .	.007/0,18				
E .117/2,97 .1	37/3,48				
F .5/2/14,50	.5/2/14,53				
G .130/3.30	.130/3.30				
н .275/6,99 .а	.285/7,24				
I 640/16,26	640/16,26				
J .175/4,45 .8	21 /75,51				

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CEO}	$I_C = 20 \text{ mA}$	25			٧
BV _{CES}	$I_C = 10 \text{ mA}$	45			٧
BV _{EBO}	$I_E = 1.0 \text{ mA}$	3.5			٧
h _{FE}	$V_{CE} = 5.0 \text{ V}$ $I_{C} = 200 \text{ mA}$	15			
C _{ob}	V _{CB} = 28 V f = 1.0 MHz			7.0	pF
P _G	V _{CF} = 28 V P _{out} = 5.0 W f = 400 MHz	10	12		dB
h _c	V CE = 20 V 1 out = 3.0 VV 1 = 400 W112	50	55		%

ADVANCED SEMICONDUCTOR, INC.